

Crystal Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Crystalline structure	-	Monocrystalline	
Growth technique	-	Czochralski (Cz)	
Orientation	-	<100> ±1°	
Slice orientation	Degrees	ON ±1.0°	
Electrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Conductance type	-	P-type	
Dopant	-	Boron	
Resistivity	Ω-cm	1 - 100	
Geometrical Properties			
PARAMETER	UNITS	SPECIFICATION	NOTE
Diameter	mm	200±0.50	
Thickness	μm	725±25	
TTV	μm	≤7	
Warp	μm	≤40	
Bow	μm	≤40	
Notch	-	SEMI Standard	
Notch depth	mm	1.0 + 0.25 – 0.00	
Notch angle	-	90° +5° -1°	
Notch orientation	-	<110>±1°	
Surface Appearance			
PARAMETER	UNITS	SPECIFICATION	NOTE
Front surface	-	Polished	
Back surface	-	Etched	
Frontside particles ≥0.08 μm (LLS)	No./wafer	≤50	
Nominal edge exclusion	mm	3.0	
Wafer Identification			
PARAMETER	UNITS	SPECIFICATION	NOTE
Lasermark	-	Frontside	
Surface Metals			
APPLICABLE METALS	UNITS	SPECIFICATION	NOTE
Al, Ca, Cl, Cr, Cu, Fe, K, Na, Ni, Zn	Atoms/cm ²	≤5E10	